3040.3



Data Sheet August 2000 File Number

Radiation Hardened 8-Bit Bus Transceiver

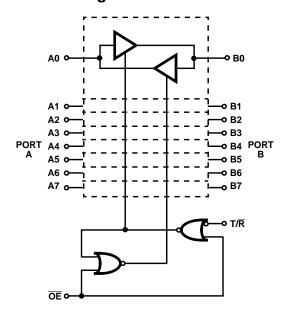
The Intersil HS-82C08RH is a radiation-hardened octal bus transceiver with three-state outputs. It is manufactured using a self-aligned, junction isolated CMOS process and is designed for use with the HS-80C08RH radiation-hardened microprocessor. The HS-82C08RH allows asynchronous two-way communication between data buses. The direction of data flow is determined by the logic level on the transmit/receive (T/\overline{R}) input. A logic high on the T/\overline{R} input specifies data flow from Port A to Port B of the device. Conversely, a logic low on the T/\overline{R} input specifies data flow from Port B to Port A. The Output Enable input disables both ports by placing them in the high impedance state.

The HS-82C08RH is ideally suited for a wide variety of buffering applications in radiation-hardened microcomputer systems.

Specifications for Rad Hard QML devices are controlled by the Defense Supply Center in Columbus (DSCC). The SMD numbers listed here must be used when ordering.

Detailed Electrical Specifications for these devices are contained in SMD 5962-95714. A "hot-link" is provided on our homepage for downloading. www.intersil.com/spacedefense/space.asp

Functional Diagram



Features

- Electrically Screened to SMD # 5962-95714
- QML Qualified per MIL-PRF-38535 Requirements
- Radiation Performance
 - Total Dose......100 krad(Si) (Max)
 - Latch-Up Immune EPI-CMOS >1 x 10¹² rad(Si)/s
- Bidirectional Three-State Input/Outputs
- · Low Propagation Delay Time
- · Low Power Consumption
- Single Power Supply +5V
- Electrically Equivalent to Sandia SA2997
- Military Temperature Range -55°C to 125°C

Ordering Information

| ORDERING NUMBER | INTERNAL MKT. NUMBER | TEMP. RANGE (°C) |
|-----------------|-------------------------|---------------------|
| 5962R9571401QRC | HS1-82C08RH-8 | -55 to 125 |
| 5962R9571401QXC | HS9-82C08RH-8 | -55 to 125 |
| 5962R9571401VRC | HS1-82C08RH-Q | -55 to 125 |
| 5962R9571401VXC | HS9-82C08RH-Q | -55 to 125 |

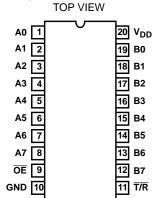
TRUTH TABLE

| INPUTS | | OPERATION | |
|------------------|----------------------|-----------|--------|
| OUTPUT ENABLE | TRANSMIT /RECEIVE | PORT A | PORT B |
| 0 | 0 | Out | In |
| 0 | 1 | In | Out |
| 1 | Х | High Z | High Z |

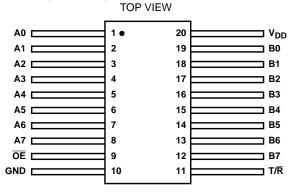
X = Don't Care

Pinouts

20 LEAD CERAMIC DUAL-IN-LINEMETAL-SEAL PACKAGE (SBDIP) MIL-STD-1835, CDIP2-T20

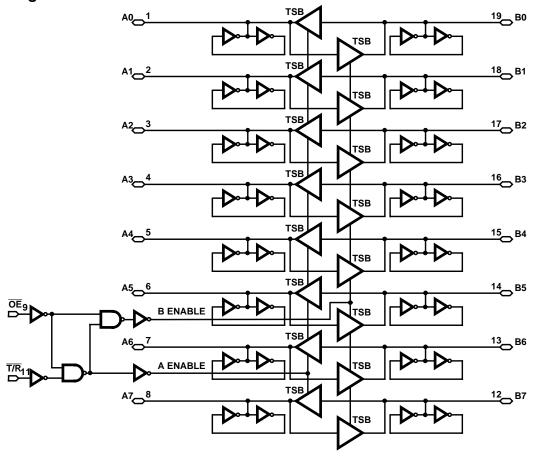


20 LEAD CERAMIC METAL SEALFLATPACK PACKAGE (FLATPACK) MIL-STD-1835, CDFP4-F20



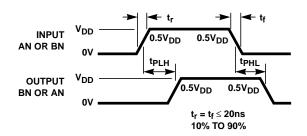
| PIN | DESCRIPTION | PIN | DESCRIPTION |
|-------|--------------------------|-----|--------------------------|
| A0-A7 | Local Bus Data I/O Pins | T/R | Transmit/Receive Input |
| B0-B7 | System Bus Data I/O Pins | ŌĒ | Active Low Output Enable |

Logic Diagram



NOTE: An Important caveat that is applicable to CMOS devices in general is that unused inputs should never be left floating. This rule applies to inputs connected to a three-state bus. The need for external pull-up resistors during three-state bus conditions is eliminated by the presence of regenerative latches on the following HS-82C08RH pins. A0-7 and B0-7 The functional block diagram depicts one of these pins with the regenerative latch. When the CMOS driver assumes the high impedance state, the latch holds the bus in whatever logic state (high or low) it was before the three-state condition. A transient drive current of ± 1.5 mA at $V_{DD}/2 \pm 0.5$ V for 10ns is required to switch the latch. Thus, CMOS device inputs connected to the bus are not allowed to float during three-state conditions.

Switching Time Waveforms



DEVICE UNDER TEST POINTS

TEST

TEST

TEST POINTS

FIGURE 1. PORT TO PORT

NOTE: C_L includes stray and jig capacitance.

FIGURE 2. AC TESTING LOAD CIRCUIT

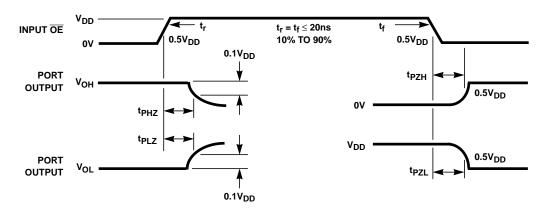


FIGURE 3. $\overline{\text{OE}}$ TO HIGH-IMPEDANCE, $\overline{\text{OE}}$ TO PORT OUTPUT

Die Characteristics

DIE DIMENSIONS:

76.0 mils x 89.4 mils x 14 mils \pm 1 mil

INTERFACE MATERIALS:

Glassivation:

Type: SiO₂

Thickness: 8kÅ ±1kÅ

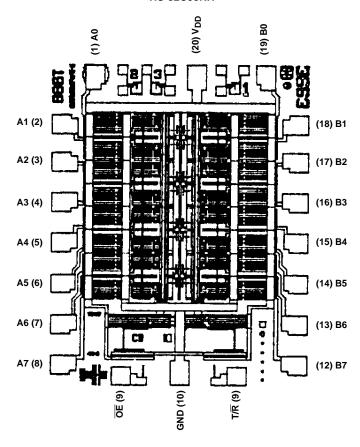
Top Metallization:

Type: Si - Al

Thickness: 11kÅ ±2kÅ

Metallization Mask Layout

HS-82C08RH



All Intersil semiconductor products are manufactured, assembled and tested under ISO9000 quality systems certification.

Intersil semiconductor products are sold by description only. Intersil Corporation reserves the right to make changes in circuit design and/or specifications at any time without notice. Accordingly, the reader is cautioned to verify that data sheets are current before placing orders. Information furnished by Intersil is believed to be accurate and reliable. However, no responsibility is assumed by Intersil or its subsidiaries for its use; nor for any infringements of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of Intersil or its subsidiaries.

For information regarding Intersil Corporation and its products, see web site www.intersil.com

Sales Office Headquarters

NORTH AMERICA

Intersil Corporation P. O. Box 883, Mail Stop 53-204 Melbourne, FL 32902

TEL: (321) 724-7000 FAX: (321) 724-7240 **EUROPE**

Intersil SA Mercure Center 100, Rue de la Fusee 1130 Brussels, Belgium

TEL: (32) 2.724.2111 FAX: (32) 2.724.22.05 **ASIA**

Intersil Ltd. 8F-2, 96, Sec. 1, Chien-kuo North, Taipei, Taiwan 104

Republic of China TEL: 886-2-2515-8508 FAX: 886-2-2515-8369